

CD4514B, CD4515B Types

CMOS 4-Bit Latch/4-to-16

Line Decoders

High-Voltage Types (20-Volt Rating)

CD4514B Output "High" on Select

CD4515B Output "Low" on Select

■ CD4514B and -CD4515B consist of a 4-bit strobed latch and a 4-to-16-line decoder. The latches hold the last input data presented prior to the strobe transition from 1 to 0. Inhibit control allows all outputs to be placed at 0 (CD4514B) or 1 (CD4515B) regardless of the state of the data or strobe inputs.

The decode truth table indicates all combinations of data inputs and appropriate selected outputs.

These devices are similar to industry types MC14514 and MC14515.

The CD4514B and CD4515B types are supplied in 16-lead hermetic dual-in-line ceramic packages (F3A suffix), 16-lead dual-in-line plastic packages (E suffix), and 16-lead small-outline packages (M and M96 suffixes).

Features:

- Strobed input latch
- Inhibit control
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V

- 5-V, 10-V, and 15-V parametric ratings
- Standardized, symmetrical output characteristics.
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Digital multiplexing
- Address decoding
- Hexadecimal/BCD decoding
- Program-counter decoding
- Control decoder

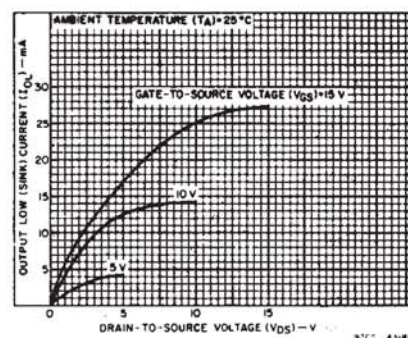
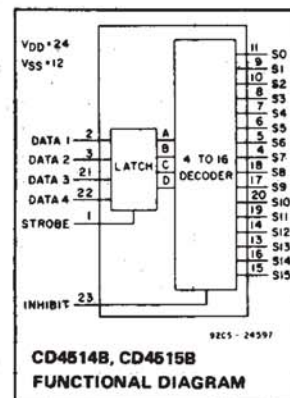


Fig. 1 – Typical output low (sink) current characteristics.

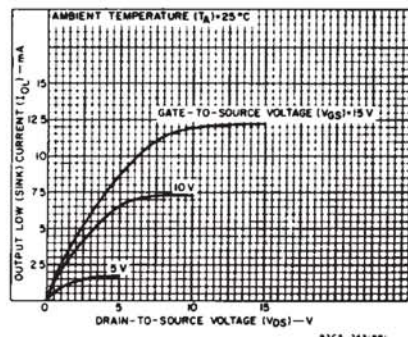


Fig. 2 – Minimum output low (sink) current characteristics.

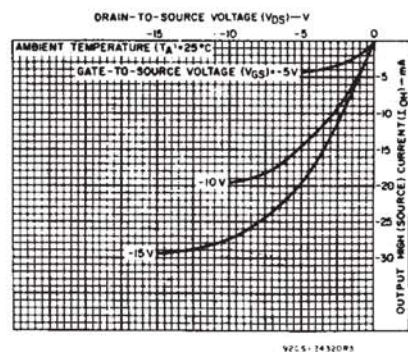


Fig. 3 – Typical output high (source) current characteristics.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5$ V

DC INPUT CURRENT, ANY ONE INPUT ± 10 mA

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearly at 12mW/ $^\circ\text{C}$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79mm) from case for 10s max $+265^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^\circ\text{C}$, Except as Noted.

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Min.	Max.	
Supply-Voltage Range (For $T_A = \text{Full Package-Temperature Range}$)		3	18	V
Data Setup Time, t_s	5	150	—	ns
	10	70	—	
	15	40	—	
Strobe Pulse Width, t_W	5	250	—	ns
	10	100	—	
	15	75	—	

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STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	+25							
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I _{DD} Max.	-	0,5	5	5	5	150	150	-	0.04	5	μA
	-	0,10	10	10	10	300	300	-	0.04	10	
	-	0,15	15	20	20	600	600	-	0.04	20	
	-	0,20	20	100	100	3000	3000	-	0.08	100	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage: Low-Level, V _{OL} Max.	-	0,5	5	0.05				-	0	0.05	V
	-	0,10	10	0.05				-	0	0.05	
	-	0,15	15	0.05				-	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	-	0,5	5	4.95				4.95	5	-	V
	-	0,10	10	9.95				9.95	10	-	
	-	0,15	15	14.95				14.95	15	-	
Input Low Voltage, V _{IL} Max.	0.5, 4.5	-	5	1.5				-	-	1.5	V
	1, 9	-	10	3				-	-	3	
	1.5, 13.5	-	15	4				-	-	4	
Input High Voltage, V _{IH} Min.	0.5, 4.5	-	5	3.5				3.5	-	-	V
	1, 9	-	10	7				7	-	-	
	1.5, 13.5	-	15	11				11	-	-	
Input Current I _{IN} Max.	-	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA

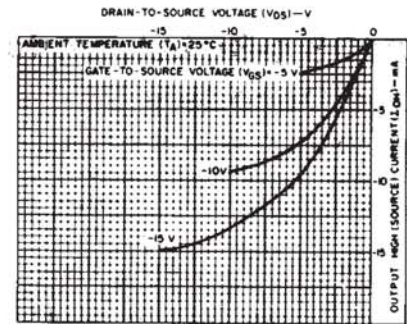


Fig. 4 — Minimum output high (source) current characteristics.

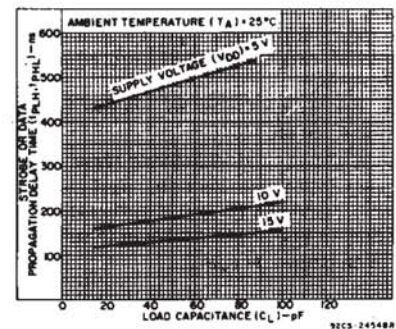


Fig. 5 — Typical strobe or data propagation delay time vs. load capacitance.

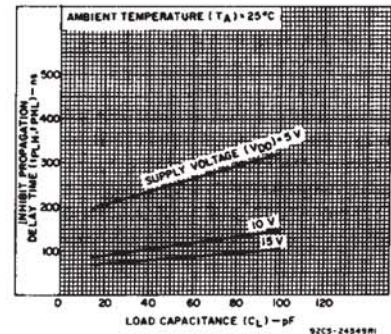


Fig. 6 — Typical inhibit propagation delay time vs. load capacitance.

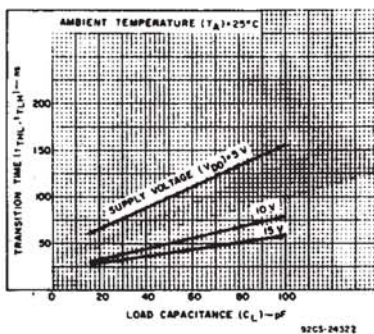


Fig. 7 — Typical low-to-high transition time vs. load capacitance.

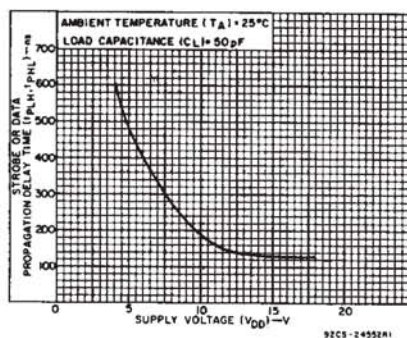


Fig. 8 — Typical strobe or data propagation delay time vs. supply voltage.

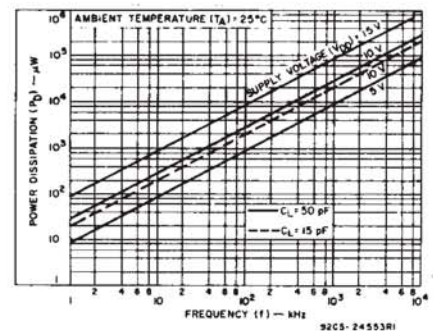


Fig. 9 — Typical power dissipation vs. frequency.

CD4514B, CD4515B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ ns}$,
 $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS			UNITS
		V_{DD} V	Typ.	Max.	
Propagation Delay Time: t_{PHL} , t_{PLH} Strobe or Data		5	485	970	ns
		10	185	370	
		15	135	270	
Inhibit		5	250	500	ns
		10	110	220	
		15	85	170	
Transition Time, t_{TLH} , t_{THL}		5	100	200	ns
		10	50	100	
		15	40	80	
Minimum Strobe Pulse Width, t_W		5	125	250	ns
		10	50	100	
		15	40	75	
Minimum Data Setup Time, t_S		5	75	150	ns
		10	35	70	
		15	20	40	
Input Capacitance, C_{IN}	Any Input	—	5	7.5	pF

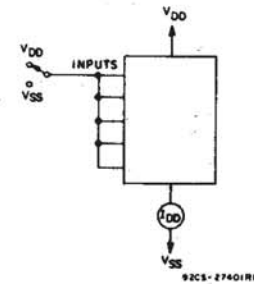


Fig. 10 — Quiescent device current test circuit.

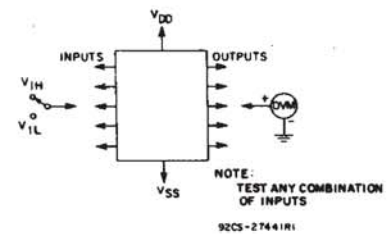


Fig. 11 — Input voltage test circuit.

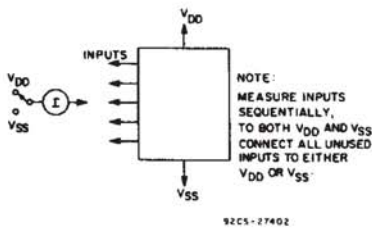


Fig. 12 — Input current test circuit.

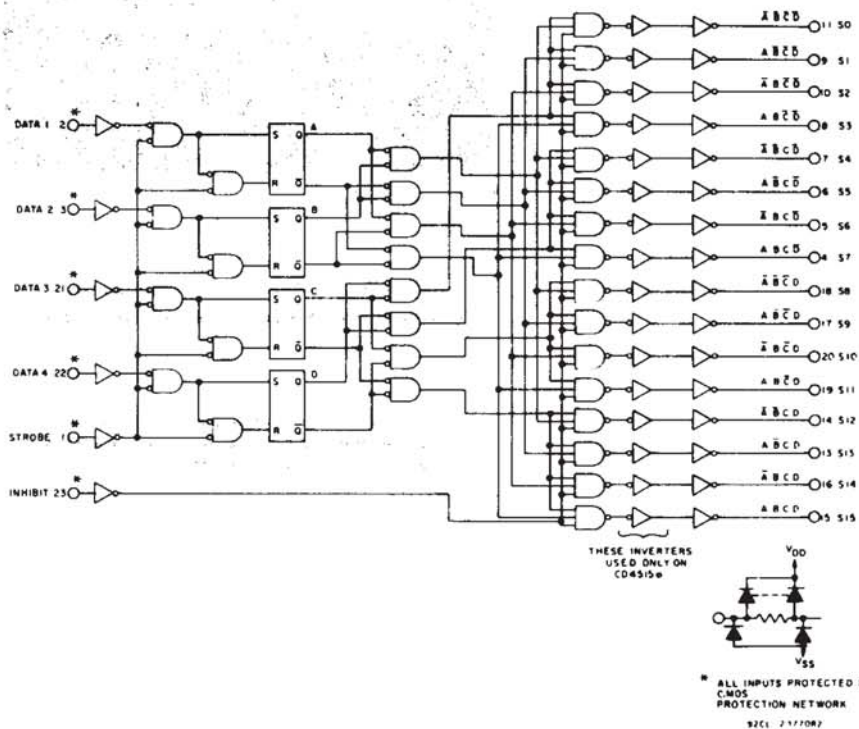


Fig. 13 — Logic diagram for CD4514B and CD4515B.

CD4514B, CD4515B Types

DECODE TRUTH TABLE (Strobe = 1)

INHIBIT	DECODER INPUTS				SELECTED OUTPUT
	D	C	B	A	
0	0	0	0	0	S0
0	0	0	0	1	S1
0	0	0	1	0	S2
0	0	0	1	1	S3
0	0	1	0	0	S4
0	0	1	0	1	S5
0	0	1	1	0	S6
0	0	1	1	1	S7
0	1	0	0	0	S8
0	1	0	0	1	S9
0	1	0	1	0	S10
0	1	0	1	1	S11
0	1	1	0	0	S12
0	1	1	0	1	S13
0	1	1	1	0	S14
0	1	1	1	1	S15
1	X	X	X	X	All Outputs = 0, CD4514B All Outputs = 1, CD4515B

X = Don't Care Logic 1 = high Logic 0 = low

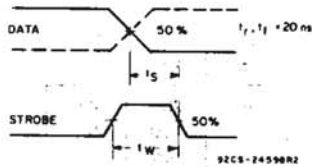
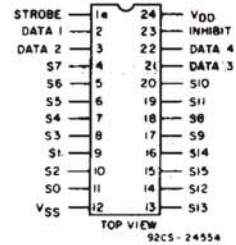
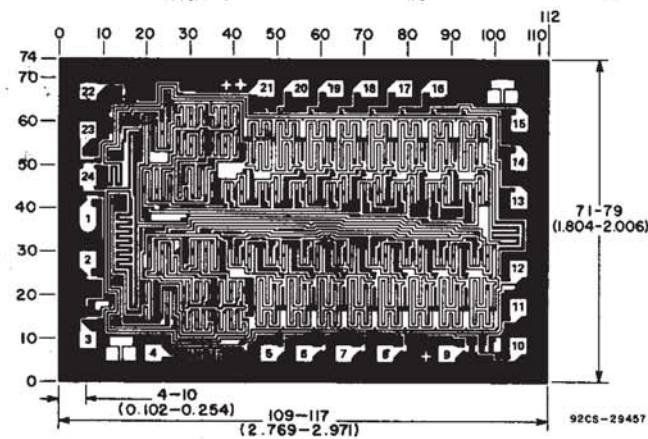


Fig. 14 — Waveforms for setup time and strobe pulse width.



CD4514B
CD4515B

TERMINAL ASSIGNMENT



Dimensions and Pad Layout for CD4515B Chip
(Dimensions and pad layout for the CD4514B are identical)

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
7703201JA	ACTIVE	CDIP	J	24	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	7703201JA CD4515BF3A	Samples
CD4514BF	ACTIVE	CDIP	J	24	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	CD4514BF	Samples
CD4514BF3A	ACTIVE	CDIP	J	24	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	CD4514BF3A	Samples
CD4514BM	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4514BM	Samples
CD4514BM96	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-55 to 125	CD4514BM	Samples
CD4514BM96E4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4514BM	Samples
CD4514BM96G4	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4514BM	Samples
CD4515BF3A	ACTIVE	CDIP	J	24	1	TBD	Call TI	N / A for Pkg Type	-55 to 125	7703201JA CD4515BF3A	Samples
CD4515BM	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4515BM	Samples
CD4515BM96	ACTIVE	SOIC	DW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4515BM	Samples
CD4515BME4	ACTIVE	SOIC	DW	24	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4515BM	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

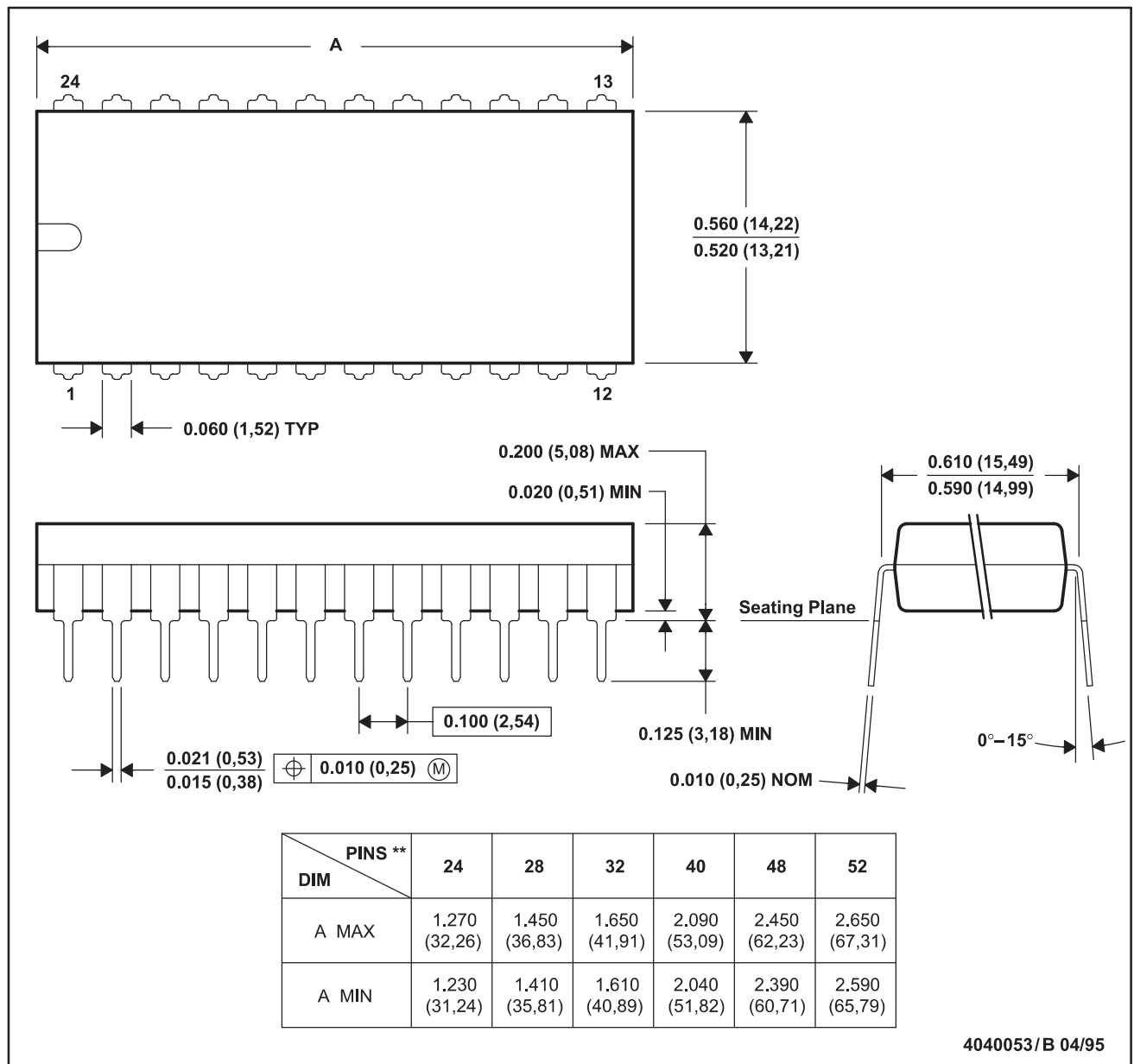
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

24 PIN SHOWN



- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Falls within JEDEC MS-011
 D. Falls within JEDEC MS-015 (32 pin only)